



Solutions for Wind Energy Systems

Energy-efficient components and subsystems for high system reliability





Contents

Introduction	3
Topologies	4
Products	8
Stacks	8
Bipolar modules and discs	10
PrimePACK™	12
IHM	14
IHV	16
EconoDUAL™ 3	18
EconoPACK™ +	20
EconoPACK™	22
EiceDRIVER™ boards	24
EiceDRIVER™ ICs	26
Microcontrollers	28
Integrated sensors	30
Linear Hall sensors	32
SmartLEWIS™ MCU	33
Online development support (IPOSIM)	34

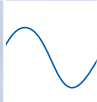


Introduction

Power semiconductors play a key role to produce energy from renewable sources. In wind turbines, power semiconductors are used to convert power and to couple the generator with the grid. They are also built into various auxiliary drives such as yaw drives, pitch drives, pumps and into protection circuits like crowbars.

Wind power converters control a number of vital functions and applications and therefore require power semiconductors of the highest quality standards. This applies in particular to offshore wind converters, which operate in exceptionally harsh environments exposed to salt, humidity etc. Rapid growth is projected for the offshore segment.

Wind energy turbines must also be designed to deliver maximum levels of availability in order to contribute to grid stability. This applies not only to the converter, but also to the various auxiliary drives mounted in different positions. Grid stability therefore depends on power semiconductor assemblies offering dynamic capabilities, outstanding functionality and superior reliability.



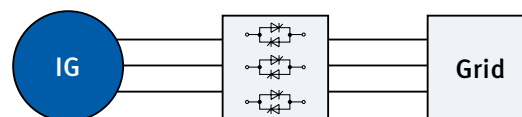
Power semiconductors:
From generator to grid



Topologies

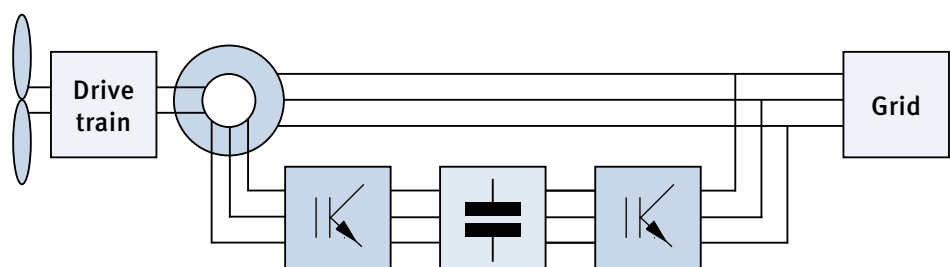
Fixed-speed generators

Fixed-speed designs are suited to generators up to 400 kW. New designs are usually based on semiconductor solutions to fulfill grid code requirements. Nevertheless, Infineon delivers the full range of grid coupling components, with thyristors and other bipolar semiconductors available as modules, discs and stacks.



Doubly Fed Induction Generator (DFIG)

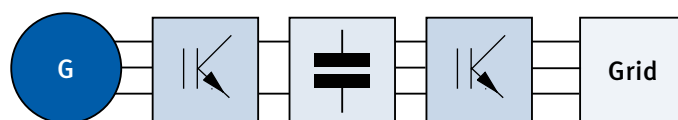
This speed-adjustable design is typically deployed in the power range between 400 kW and 2.500 kW. To control the full load only up to one third of the energy needs to be converted over power semiconductors in both directions. Infineon's IGBTs support optimum performance even at the limits of the operating range. High quality design, low voltage ride through (LVRT) capability and very low output frequencies meet high availability needs.





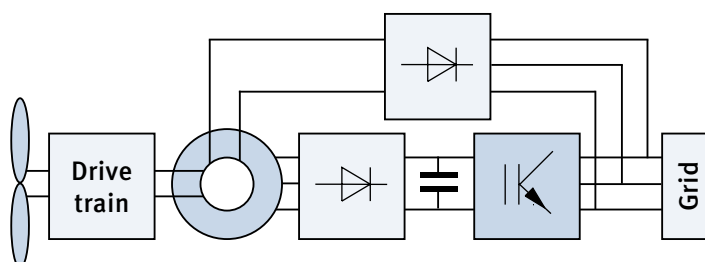
Permanent Magnet (PM) generators

Full converters for low-, medium- and high-speed generators provide maximum flexibility to meet LVRT and other grid stability requirements. High efficiency is mandatory and an active front-end inverter adapts variable power and frequency. This design reduces inductive component effort. Infineon's IGBTs enable modular and scalable system designs.



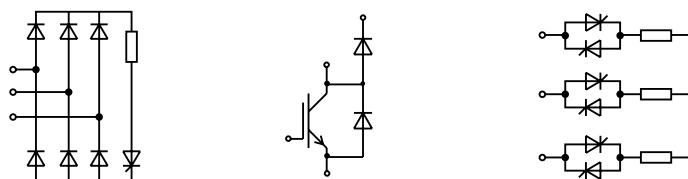
Electrical Excited (EE) generators

An EE generator feeds the inverter via a bipolar rectifier, with the generator voltage controlled by excitation. The grid inverter is controlled by an IGBT as the effect of excitation. This design is an established solution already successfully deployed in modern systems.



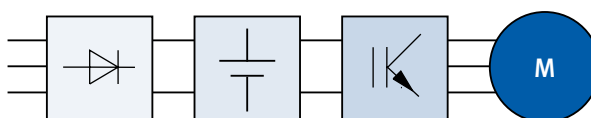
Protection circuits

Crowbars, choppers and active filters are important elements in wind turbine designs. Even though these components are not actively involved in feeding energy, they are needed to manage external impacts and fulfill grid stability requirements.



Auxiliary drives

Several drives are needed for a wind turbine design to function safely and properly. Yaw drives, pitch drives and pumps can be controlled by small inverters. An energy storage solution must be connected to the DC link in pitch control drives to enable emergency shutdown.





Overview of products supplied by Infineon

Inverter (p. 4/5)

Application	Stacks (p. 8)	IHM (p. 14)	PrimePACK™ (p. 12)	IHV (p. 16)	EconoDUAL™ 3 (p. 18)	EconoPACK™ + (p. 20)	Bipolar (p. 10)	Driver boards 2ED300C17 (p. 24)
PM (p. 5)	✓	✓	✓	✓	✓	✓	–	✓
DFIG (p. 4)	✓	✓	✓	✓	✓	✓	–	✓
EE (p. 5)	✓	✓	✓	✓	✓	✓	✓	✓

Protection circuits (p. 5)

Application	Stacks (p. 8)	IHM (p. 14)	Bipolar (p. 10)
Choppers	✓	✓	–
Crowbars	✓	–	✓

Auxiliary drives (p. 5)

Application	Low Power Econos (p. 22)	EconoDUAL™ 3 (p. 18)	Driver ICs 1ED020I12-B2 (p. 26)
Pitch control	✓	✓	✓
Yaw control	✓	✓	✓
Pump control	✓	✓	✓



Highest energy efficiency

Wide portfolio designed for the highest energy efficiency levels.

Our TRENCHSTOP™ IGBT with its trench gate and field stop concept has dramatically improved the static and dynamic losses of IGBT designs. This improved performance has made our power switches more efficient, increasing power density up to 50 percent. In addition, our zero defect strategy, coupled with the experience gained producing more than 1 million TRENCHSTOP™ IGBT wafers to date, is the best guarantee of lowest failure rates and highest reliability.

Key benefits:

- Industry-leading maximum operating junction temperature of 150°C
- Improved performance with lower electrical losses
- IGBT power modules offering highest quality and reliability

We have a global team of experienced application engineers providing advanced and cost-effective reference solutions and design support for our customers, thereby facilitating and shortening their time-to-market.

Environmental sustainability

- We have integrated environmental sustainability in our daily business and our strategy.
- We constantly reduce our environmental footprint.
- We enable energy-efficient end-products and applications.
- We enable a sustainable society by providing net environmental benefits.

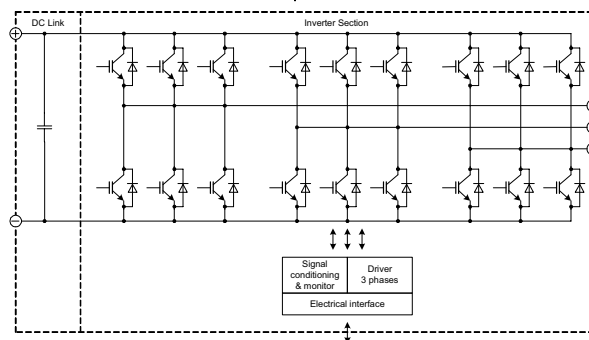
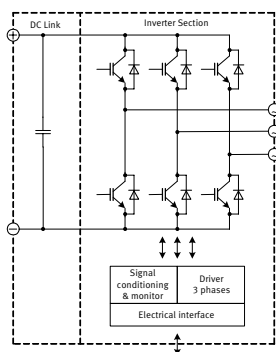


Stacks

Our ModSTACK™ HD family is a complete power electronic switch assembly including our standard PrimePACK™ high-power IGBT half-bridge modules. The family supports nominal chip currents from 1000 A up to 3000 A at 1700 V. The standard switch assemblies are equipped with the necessary components for current, voltage and temperature measurement. Features include monitoring functions for self-protection and liquid cooled heat sinks for thermal management with optimized performance. Vertically arranged AC power terminals are mechanically decoupled from the power terminals of the modules to give our customers maximum flexibility when connecting the power bus system.

Key benefits

- Highest power density with PrimePACK™ IGBT4 modules
- Wide product range supporting all applications
- Suited to standardized cabinet frame size
- High reliability and robust design
- Parallel operation possible
- Increased operating temperature $T_{vjop} = 150^{\circ}\text{C}$ with new IGBT4
- Low stray inductance
- Improved power cycling and thermal cycling capability
- Enlarged clearance and creepage distances
- Internal NTC sensor



The ModSTACK™ HD stack works as a sub-assembly in a full converter system. The general control signals are supplied by a higher-level control unit provided by the customer. The ModSTACK™ HD family provides proven industry-standard electrical interfaces for regular operation and fault signal management. The ModSTACK™ HD can work in stand-alone or parallel mode (master/slave configuration). Up to 8 MW is possible by paralleling up to 4 sub-assemblies. Symmetrical power layout and PWM control has to be provided by the end user. Our ModSTACK™ HD family provides reliable and outstanding stack quality with optimized thermal management. The latest IGBT4 chip technology, combined with an in-built electronic controller and an optimized cooling concept, make this innovative solution ideal for a broad range of wind power systems.



IGBT4 1700V_{CES}
 $V_{AC} = 690V_{RMS} / V_{DC} = 1100V$

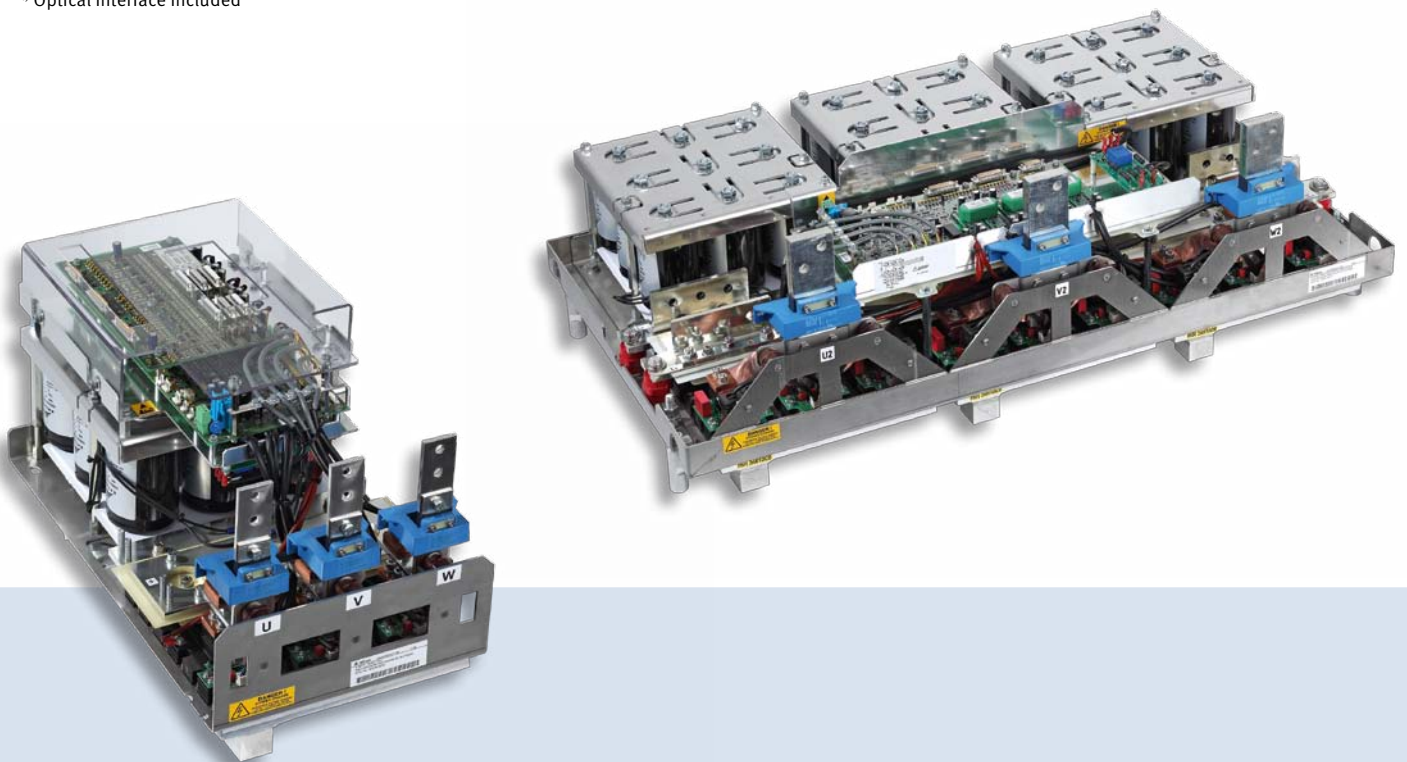
$P_{max}^{3)}$ [kW]	$I_{RMS}^{1)}$ [A]	f_{SW} [kHz]	$f_{SWmax}^{2)}$ [kHz]	Stack type	Implemented IGBT4 modules	Topology	Case cooling	Width x depth x height [mm]
609	600	3	5	6MS10017E41W36460	3 x FF1000R17IE4	B6I	MS HD1 liquid (copper)	338 x 590 x 350
691	680	3	5	6MS10017E41W36775	3 x FF1000R17IE4	B6I	MS HD1 liquid (aluminum)	338 x 590 x 375
1219	1200	3	4	6MS20017E43W37032	6 x FF1000R17IE4	B6I	MS HD3 liquid (copper)	1090 x 596 x 342
1219	1200	3	4	6MS20017E43W38170 ⁴⁾	6 x FF1000R17IE4	B6I	MS HD3 liquid (copper)	1090 x 596 x 342
1828	1800	3	3	6MS30017E43W35613	9 x FF1000R17IE4	B6I	MS HD3 liquid (copper)	1090 x 596 x 342
1828	1800	3	4	6MS30017E43W38169 ⁴⁾	9 x FF1000R17IE4	B6I	MS HD3 liquid (copper)	1090 x 596 x 342
1828	1800	3	3	6MS30017E43W33015	9 x FF1000R17IE4	B6I	MS HD3 liquid (aluminum)	1090 x 596 x 342
2082	2050	3	3	6MS30017E43W34404	9 x FF1000R17IE4	B6I	MS HD3 liquid (aluminum)	1090 x 596 x 366
691 1382	680 1360	3 3	8 4	12MS20017E43W35155	3 x FF1000R17IE4 6 x FF1000R17IE4	B6I + B6I	MS HD3 liquid (aluminum)	1090 x 596 x 342

¹⁾ Typical output current at $V_{DC}=1100V$, $V_{AC}=690V$, $f_{SW}=3$ kHz, $f_o=50Hz$, $\cos(\varphi)=0.85$, $T_A=40^\circ C$, $T_{vjmax} \leq 150^\circ C$.

²⁾ Current derating may be required

³⁾ P_{max} for 3-phase system similar to B6I types

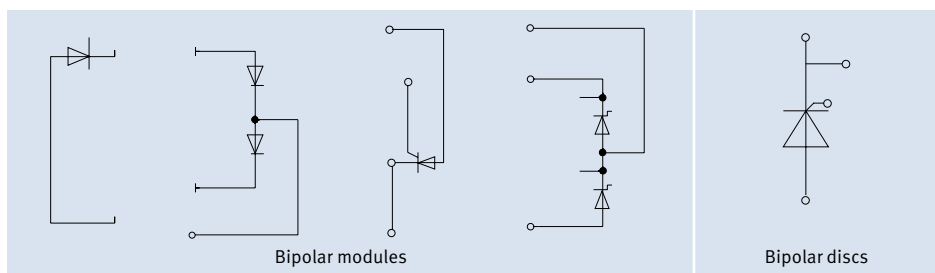
⁴⁾ Optical interface included





Bipolar modules and discs

The availability and reliability of power semiconductors incorporated in wind power applications are key success factors for the overall design. Our bipolar modules and discs are ideal for these harsh environments with their rugged, highly reliable pressure contact technologies. In today's windmill systems, they are used as input thyristors and generator voltage rectifiers, in auxiliary power supplies and in protective crowbar applications. The low-maintenance design, high quality and exceptional reliability of our bipolar devices ensure profitable operation over a long lifetime.



Key benefits

- Short on fail
- High overload capability
- High reliability and long lifetime
- Lowest maintenance costs





Type	V_{RRM} [V]	I_{FSM} [A] @10 ms, $T_{vj\ max}$	$\int i^2 dt$ [A ² · s · 10 ³] @10 ms, $T_{vj\ max}$	I_{FAVM}/T_c [A] @180° el sin	$V_{(TO)}$ [V] $T_{vj\ max}$	r_T [mΩ] $T_{vj\ max}$	$R_{thJC\ max}$ [K/W] @180° el sin	R_{thch} [K/W] @180° el sin	$T_{vj\ max}$ [°C]
DZ 540 N26 K	2600	14000	980	540/100	0.78	0.31	0.078	0.02	150
DD 700 N22 K	2200	21000	2205	700/100	0.78	0.19	0.065	0.02	150
DZ 1070 N26 K	2600	35000	6125	1070/100	0.80	0.17	0.045	0.01	160

Type	V_{DRM}, V_{RRM} [V] $V_{DSM} = V_{DRM}$ $V_{RSM} = V_{RRM} + 100\ V$	I_{TSM} [A] @10 ms, $T_{vj\ max}$	$\int i^2 dt$ [A ² · s · 10 ³] 10 ms, $T_{vj\ max}$	I_{TAVM}/T_c [A/°C] @180° el sin	$V_{(TO)}$ [V] @ $T_{vj\ max}$	r_T [mΩ] @ $T_{vj\ max}$	$(di/dt)_cr$ [A/μs] @DIN IEC 747-6	t_q [μs] typ.	$R_{thJC\ max}$ [K/W] @180° el sin	R_{thCK} [K/W] @180° el sin	$T_{vj\ max}$ [°C]
TZ 749 N22 KOF	2200	26500	3500	740/85	0.90	0.21	200	350	0.042	0.01	125
TZ 800 N18 KOF	1800	30000	4500	800/85	0.85	0.17	200	240	0.042	0.01	125
TT 425 N18 KOF	1800	12500	781	425/85	0.90	0.30	120	250	0.078	0.02	125
TT 430 N22 KOF	2200	12000	720	430/85	0.95	0.45	150	300	0.065	0.02	125
TT 500 N18 KOF	1800	14500	1051	500/85	0.90	0.27	200	250	0.065	0.02	125
TT 520 N22 KOF	2200	14500	1051	520/85	0.85	0.35	200	250	0.058	0.02	125

Type	V_{DRM}, V_{RRM} [V] $V_{DSM} = V_{DRM}$ $V_{RSM} = V_{RRM} + 100\ V$	I_{TSM} [kA] @10 ms, $T_{vj\ max}$	$\int i^2 dt$ [A ² · s · 10 ³] @10 ms, $T_{vj\ max}$	V_T/I_T [V/kA] $T_{vj\ max}$	I_{TAVM} [A] @180° el sin $T_c = 85\ ^\circ\text{C}$	$V_{(TO)}$ [V] @ $T_{vj\ max}$	r_T [mΩ] @ $T_{vj\ max}$	$(di/dt)_cr$ [A/μs] @DIN IEC 747-6	t_q [μs] typ.	$R_{thJC\ max}$ [K/kW] @180° el sin	$T_{vj\ max}$ [°C]
T 1190 N18 TOF VT	1800	22.5	2530	2.05/5.4	1190	0.90	0.190	200	240	23.0	125
T 1500 N18 TOF VT	1800	33.5	5611	2.10/7.0	1500	0.90	0.150	200	240	18.4	125
T 2180 N18 TOF VT	1800	36.0	6480	2.05/8.0	2180	0.90	0.106	200	250	12.5	125
T 3160 N18 TOF VT	1800	57.0	16245	1.37/6.0	3160	0.85	0.082	200	250	8.5	125





PrimePACK™

Our PrimePACK™ IGBT modules in half-bridge and chopper configurations (1200V & 1700V, 450A to 1400A) with internal NTC have been optimized for modern converters. Key highlights include improved thermal properties, low stray inductance and a wide range of operating temperatures up to 150°C.

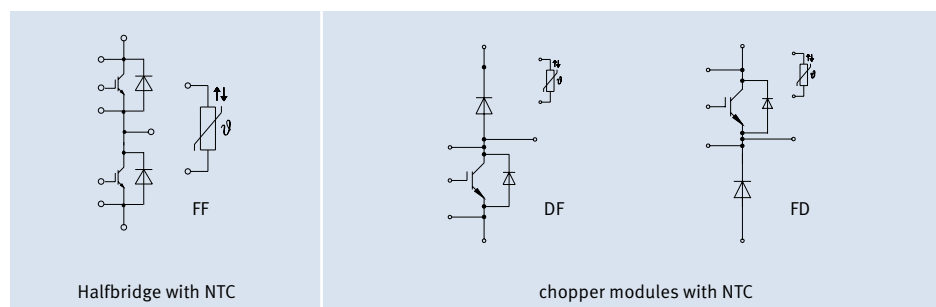
This family is designed to support inverter designs across a broad power range. The excellently placed DC terminal screw connections (all terminals are screw-connected) ensure high parallel design flexibility.

Two chopper variants (high side and low side) give design engineers even greater flexibility when choosing the inverter topology.

Many years of experience, a proven track record in driving innovation and a selection of the most recent chip generations optimized for high power applications mean that customers can always rely on us for the best converter solutions for wind applications.

Key benefits

- High power density for compact inverter designs
- Modular design optimized for paralleling
- Improved power cycling and thermal cycling capability
- Homogenous temperature distribution between the chips
- High clearance and creepage distance
- High reliability and robust module construction
- Standardized housing



Our PrimePACK™ housing enjoys broad market acceptance and has established itself as an industry standard, used by all well-known manufacturers across countless applications worldwide.



Type	V_{CES} V	I_C A	V_{CESat} V $T_{vj} = 25^\circ\text{C typ.}$	E_{on}/E_{off} mWs $T_{vj} = 125^\circ\text{C typ.}$	$R_{thjc max}$ K/W per arm
FF1000R17IE4	1700	1000	2	390/295	0.024
FF1000R17IE4D_B2	1700	1000	2	365/315	0.024
FF1400R17IP4	1700	1400	1.75	500/625	0.015
FD1000R17IE4	1700	1000	2	390/295	0.024
DF1000R17IE4	1700	1000	2	390/295	0.024
FD1000 R17IE4D_B2	1700	1000	2	365/315	0.024
DF1000 R17IE4D_B2	1700	1000	2	365/315	0.024





IHM

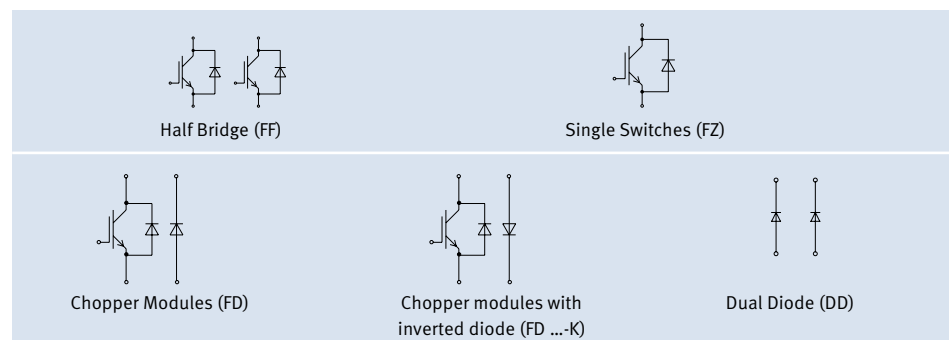
Our well-known IHM (IGBT High-power Modules) are extremely robust, operating with supreme reliability at temperatures from -40 to +150°C. These devices enjoy widespread market acceptance with more than 2 million IHMs deployed in different applications around the globe.

Highlights include superior power cycling with the latest IGBT technology and optimized switching losses. IHMs are available in 1200 V and 1700 V variants in half-bridge, single switch, chopper and diode topologies, covering a range from 400 A to 3600 A. This gives engineers the freedom to design high-power inverters of varying sizes. Electrical separation between the power and auxiliary terminals reduces the stray inductance influence on the sense contacts and makes these modules both easy to control and safe to use.

Backed by our global design support, our IHM solutions are the preferred choice for powerful, compact and modular converter designs. Customers can also rely on us to continually enhance IHM thermal properties and performance.

Key benefits

- Low V_{CEsat} and R_{thj-c}
- Superior power cycling with IGBT4
- Optimized switching losses combined with soft switching
- Widest product portfolio available in the market
 - Two housings: IHM A and IHM B
 - Two footprints: 190 x 140 mm, 130 x 140 mm
 - Two base-plate materials: AlSiC and Cu
 - I_{Cmax} from 400 A to 3600 A in voltage category 1200 V and 1700 V
 - Various topologies (half bridge-, single switch-, chopper- and diode modules)





Modul name	Green	Modul type	C-E-blocking-voltage	max. DC-rated current	Base plate	Housing
DD1200S17H4_B2	✓RoHS	Dual Diode	1700V	1200 A	AlSiC	130 x 140 mm
DD800S17H4_B2	✓RoHS	Dual Diode	1700V	800 A	AlSiC	130 x 140 mm
FD1200R17HP4-K_B2	✓RoHS	Chopper	1700V	1200 A	AlSiC	130 x 140 mm
FD1600/1200R17HP4_B2	✓RoHS	Chopper	1700V	1600 A	AlSiC	190 x 140 mm
FF800R17KP4_B2		Half bridge	1700V	800 A	AlSiC	130 x 140 mm
FF1200R17KP4_B2		Half bridge	1700V	1200 A	AlSiC	130 x 140 mm
FZ1200R12HP4		Single switch	1200V	1200 A	Cu	130 x 140 mm
FZ1600R12HP4		Single switch	1200V	1600 A	Cu	130 x 140 mm
FZ2400R12HP4		Single switch	1200V	2400 A	Cu	130 x 140 mm
FZ3600R12HP4		Single switch	1200V	3600 A	Cu	190 x 140 mm
FZ1200R17HP4		Single switch	1700V	1200 A	Cu	130 x 140 mm
FZ1600R17HP4		Single switch	1700V	1600 A	Cu	130 x 140 mm
FZ2400R17HP4		Single switch	1700V	2400 A	Cu	130 x 140 mm
FZ2400R17HP4_B9		Single switch	1700V	2400 A	Cu	190 x 140 mm
FZ3600R17HP4		Single switch	1700V	3600 A	Cu	190 x 140 mm
FZ1600R17HP4_B2	✓RoHS	Single switch	1700V	1600 A	AlSiC	130 x 140 mm
FZ1600R17HP4_B21	✓RoHS	Single switch	1700V	1600 A	AlSiC	130 x 140 mm
FZ2400R17HP4_B2	✓RoHS	Single switch	1700V	2400 A	AlSiC	130 x 140 mm
FZ2400R17HP4_B28	✓RoHS	Single switch	1700V	2400 A	AlSiC	190 x 140 mm
FZ2400R17HP4_B29	✓RoHS	Single switch	1700V	2400 A	AlSiC	190 x 140 mm
FZ3600R17HP4_B2	✓RoHS	Single switch	1700V	3600 A	AlSiC	190 x 140 mm





IHV

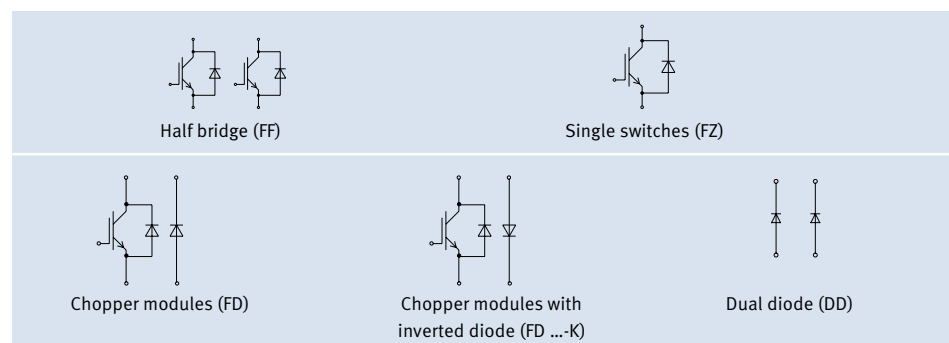
Our IHV (IGBT High-Voltage) modules are ideal for full inverter solutions in the power range above 2 MW. They enable significant cabling savings in turbine designs where the transformer is installed at the base of the tower. Our IHV devices offer blocking voltages of 3300V, 4500V or 6500V. These devices have been successfully deployed in traction applications and industrial medium-voltage inverters for many years.

Our broad portfolio supports a wide range of nominal currents, topologies (chopper, diode) and designs. Multilevel inverters such as the popular NPC (Neutral Point Clamped) model can be built with good scalability. Internal isolation enables designs with grounded heat sinks, eliminating the need for deionized cooling fluids.

Our application support team provides assistance anywhere in the world, helping in particular to resolve your paralleling, Low Voltage Ride Through (LVRT) and lifetime challenges.

Key benefits

- Low V_{CEsat} and R_{thj-c}
- Good thermal cycling capability due to AlSiC baseplate
- Optimized switching losses
- Widest portfolio on the market
 - Two housings for different isolation requirements
 - Two footprints
190x140 mm²
130x140 mm²
 - I_{Cmax} from 200 A to 1500 A
- Various topologies (half bridge-, single switch-, chopper- and diode modules)





Modul name	Green	Modul type	E-blocking-voltage	max. DC-rated current	Base plate	Housing
DD500S33HE3		Dual diode	3300V	500 A	AlSiC	130 x 140 mm
DD800S33K2C		Dual diode	3300V	800 A	AlSiC	130 x 140 mm
DD1200S33K2C		Dual diode	3300V	1200 A	AlSiC	130 x 140 mm
DD400S45KL3_B5		Dual diode	4500V	400 A	AlSiC	130 x 140 mm
DD1200S45KL3_B5		Dual diode	4500V	1200 A	AlSiC	130 x 140 mm
DD400S65K1		Dual diode	6500V	400 A	AlSiC	130 x 140 mm
DD600S65K1		Dual diode	6500V	600 A	AlSiC	130 x 140 mm
DD750S65K3		Dual diode	6500V	750 A	AlSiC	130 x 140 mm
FF400R33KF2C		Half bridge	3300V	400 A	AlSiC	130 x 160 mm
FZ800R33KF2C		Single switch	3300V	800 A	AlSiC	130 x 140 mm
FZ1000R33HE3		Single switch	3300V	1000 A	AlSiC	130 x 140 mm
FZ1000R33HL3		Single switch	3300V	1000 A	AlSiC	130 x 140 mm
FZ1200R33HE3		Single switch	3300V	1200 A	AlSiC	190 x 140 mm
FZ1500R33HE3		Single switch	3300V	1500 A	AlSiC	190 x 140 mm
FZ1500R33HL3		Single switch	3300V	1500 A	AlSiC	190 x 140 mm
FZ800R45KL3_B5		Single switch	4500V	800 A	AlSiC	130 x 140 mm
FZ1200R45KL3_B5		Single switch	4500V	1200 A	AlSiC	190 x 140 mm
FZ400R65KF2		Single switch	6500V	400 A	AlSiC	130 x 140 mm
FZ600R65KE3		Single switch	6500V	600 A	AlSiC	190 x 140 mm
FZ750R65KE3		Single switch	6500V	750 A	AlSiC	190 x 140 mm





EconoDUAL™ 3

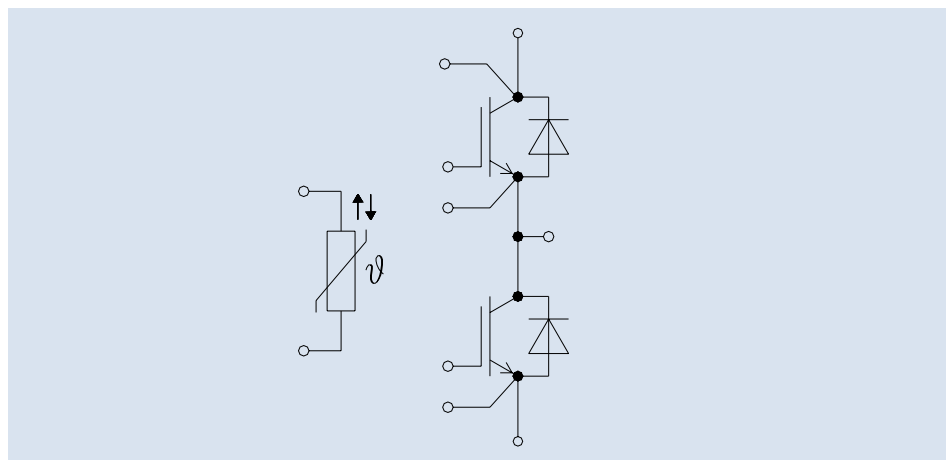
Our EconoDUAL™ 3 devices meet growing demands for compact inverter designs, flexibility and optimized electrical performance at highest reliability. These modules combine 17 mm housing with screw power terminals and easy assembly. The gate driver can be easily connected by placing it on top of the module. Low parasitic stray inductance and optimized thermal resistance to the heat sink contribute to excellent inverter designs.

All modules are available with our established PressFIT technology for reliable, solderless mounting. They are equipped with state-of-the-art IGBT4 technology up to $T_{vjop} = 150^{\circ}\text{C}$ for highest power densities and leading-edge power cycling capability – making these devices ideal for wind inverters. Symmetrical module design facilitates parallel operation, optimizing current sharing between IGBT half-bridges. This makes EconoDUAL™ 3 the compact solution of choice for 690V drives.

The FF600R17ME4/_B11 is our new flagship product in the EconoDUAL™ 3 family. It was developed with a view to maximizing power density within a given footprint. Copper bonding technology and an improved DCB combine to increase the output power by more than 30 % compared with the 450 A 1700V version.

Key benefits

- Compact modules measuring only 17 mm in height
- Easy and most reliable assembly: PressFIT controls pins and screw power terminals for completely solderless connections
- Easy separation of DC and AC link
- No plugs or cables required
- Optimized thermal resistance to heat sink
- Ideal for low inductive system designs
- Highest power density for compact inverter designs





IGBT4

Product type	Product status	Green	I_c	$V_{CE(sat)}$ (typ)	Configuration	Technology	Housing
FF600R17ME4	In production	 RoHS	600.0A	1.95V	dual	IGBT4	EconoDUAL™ 3
FF600R17ME4_B11	In production	 RoHS	600.0A	1.95V	dual	IGBT4	EconoDUAL™ 3
FF450R17ME4	In production	 RoHS	450.0A	1.95V	dual	IGBT4	EconoDUAL™ 3
FF450R17ME4_B11	In production	 RoHS	450.0A	1.95V	dual	IGBT4	EconoDUAL™ 3
FF300R17ME4	In production	 RoHS	300.0A	1.95V	dual	IGBT4	EconoDUAL™ 3
FF300R17ME4_B11	In production	 RoHS	300.0A	1.95V	dual	IGBT4	EconoDUAL™ 3
FF225R17ME4	In production	 RoHS	225.0A	1.95V	dual	IGBT4	EconoDUAL™ 3
FF225R17ME4_B11	In production	 RoHS	225.0A	1.95V	dual	IGBT4	EconoDUAL™ 3





EconoPACK™ +

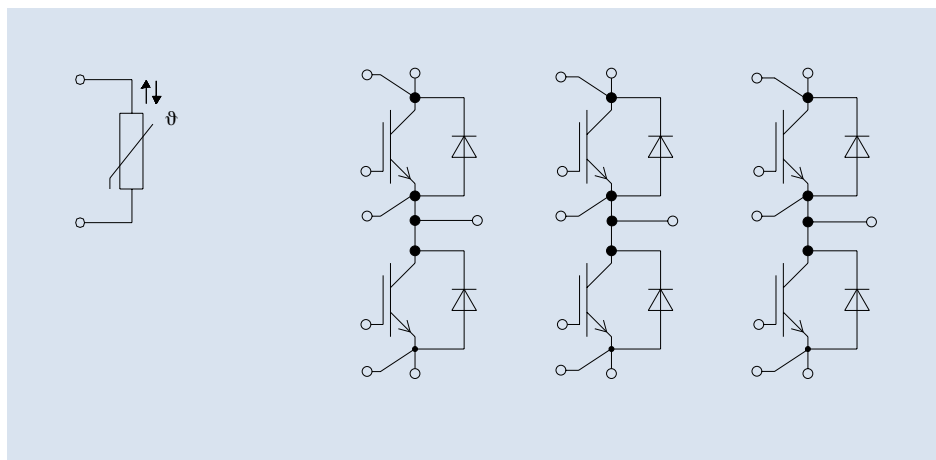
Our EconoPACK™ + D series meets growing market demands for compact inverter designs, flexibility and optimized electrical performance at highest reliability. These modules combine 17 mm housing with screw power terminals and easy assembly. The gate driver can be easily connected by placing it on top of the module. Low parasitic stray inductance and optimized thermal resistance to the heat sink contribute to excellent inverter designs.

All modules are available with our established PressFIT technology for reliable, solderless mounting. They are equipped with the state-of-the-art IGBT4 technology up to $T_{vjop} = 150^{\circ}\text{C}$ for highest power densities and leading-edge power cycling capability – making these devices ideal for wind inverters. Symmetrical module design facilitates parallel operation, optimizing current sharing between IGBT half-bridges. This makes EconoPACK™ + D the compact solution of choice for wind inverters.

The EconoPACK™ + D series is also available with our innovative pre-applied thermal interface material (TIM) solution. It fulfills the most stringent quality standards for power modules, offering the highest system reliability and output power.

Key benefits

- Compact modules measuring only 17 mm in height
- Easy and most reliable assembly: PressFIT controls pins and screw power terminals for completely solderless connections
- Easy separation of DC and AC link
- No plugs and cables required
- Optimized thermal resistance to heat sink
- Ideal for low inductive system designs
- Highest power density for compact inverter designs





IGBT4

Product type	Product status	Green	I_c	$V_{CE(sat)}$ (typ)	Configuration	Technology	Housing
FS500R170E4D	In production	 RoHS	500.0 A	1.95 V	sixpack	IGBT4	EconoPACK™ +
FS500R170E4DP	In production	 RoHS	500.0 A	1.95 V	sixpack	IGBT4	EconoPACK™ +
FS450R170E4	In production	 RoHS	450.0 A	1.95 V	sixpack	IGBT4	EconoPACK™ +
FS300R170E4	In production	 RoHS	300.0 A	1.95 V	sixpack	IGBT4	EconoPACK™ +
FS225R170E4	In production	 RoHS	225.0 A	1.95 V	sixpack	IGBT4	EconoPACK™ +





EconoPACK™

Our EconoPIM™/EconoPACK™ family was developed to give customers the option of cost-effective, compact designs with the added bonus of simplified, reliable mounting. This optimized family is targeted at low- and medium-power industrial drives used for pitch control in modern windmills.

The Econo family extends the power range from 15 A up to 200 A at 600V/650V/1200V/1700V. Devices are available in the well-known EconoPIM™ and EconoPACK™ packages. The Econo housing comes with a copper baseplate for optimized heat spread and greater reliability. It also includes a thermistor (NTC) for internal temperature measurement. Econo modules are available with solder or PressFIT pins.

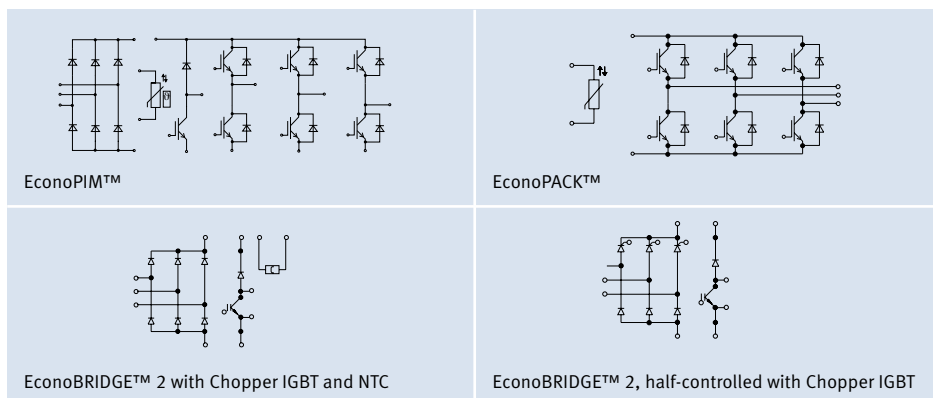
The Econo family features state-of-the-art IGBT4 650V/1200V/1700V chip technology for low switching losses, low saturation voltage and high switching frequency. For ease of design, IGBTs with 10 µs short-circuit robustness are available in the same mechanical layouts for 650V, 1200V and 1700V.

EconoBRIDGE™ 2 rectifier modules

EconoBRIDGE™ 2 rectifier modules are available in the current range from 104 A to 180 A at 1600V/1800V. The available configurations are uncontrolled or half-controlled rectifier bridges including brake chopper IGBT and thermal resistor (NTC).

Key Benefits

- Compact, well established module concept
- Optimized development cycle time and cost
- Configuration flexibility
- High power density
- Low stray inductance
- RoHS-compliant/UL recognized





	Article	IGBT inverter				Rectifier diodes				Brake chopper		
		V _{CE} [V]	I _C [A]	R _{thjC max} [K/W]	V _{CEsat} T _{vj} =25C° [V]	V _{RRM} [V]	I _g /T _c [A]/[C°]	R _{thjC max} [K/W]	V _f T _{vj} =150C° [V]	V _{CES} [V]	I _C IGBT T _c =80C° [A]	R _{thjC max} [K/W]
EconoPACK™												
650V	FS75R07N2E4	650	75	0.60	1.55							
	FS100R07N2E4	650	100	0.45	1.55							
	FS150R07N3E4	650	150	0.35	1.55							
	FS200R07N3E4R	650	200	0.25	1.55							
1200V	FS75R12KT4_B15	1200	75	0.39	1.85							
	FS100R12KT4G	1200	100	0.29	1.75							
	FS150R12KT4	1200	150	0.20	1.75							
	FS200R12KT4R	1200	200	0.15	1.75							
1700V	FS100R17N3E4	1700	100	0.25	1.95							
	FS150R17N3E4	1700	150	0.18	1.95							
EconoPIM™												
650V	FP75R07N2E4	650	75	0.60	1.55	1600	80/80	0.65	1.00	650	50	0.80
	FP100R07N3E4	650	100	0.45	1.55	1600	100/80	0.50	1.10	650	75	0.60
	FP150R07N3E4	650	150	0.35	1.55	1600	150/80	0.40	1.10	650	100	0.45
1200V	FP75R12KT4	1200	75	0.39	1.85	1600	140/80	0.65	1.15	1200	50	0.54
	FP100R12KT4	1200	100	0.29	1.75	1600	150/80	0.40	1.00	1200	50	0.54
EconoBRIDGE™												
1600V	DDB6U104N16RR					1600	105/100	1.08	1.30	1200	50	0.38
	DDB6U134N16RR					1600	134/100	0.70	1.35	1200	70	0.25
	TDB6HK124N16RR					1600	125/85	0.63	1.35 (125C°)	1200	70	0.25
	TDB6HK180N16RR					1600	180/80	0.35	1.20	1200	100	0.29
1800V	DDB6U104N18RR					1800	105/100	1.08	1.30	1200	50	0.38

Extract from our Econo 2/3 product portfolio suitable for pitch-control drives. All modules also available in PressFIT technology (EconoBRIDGE™ <180A on request)



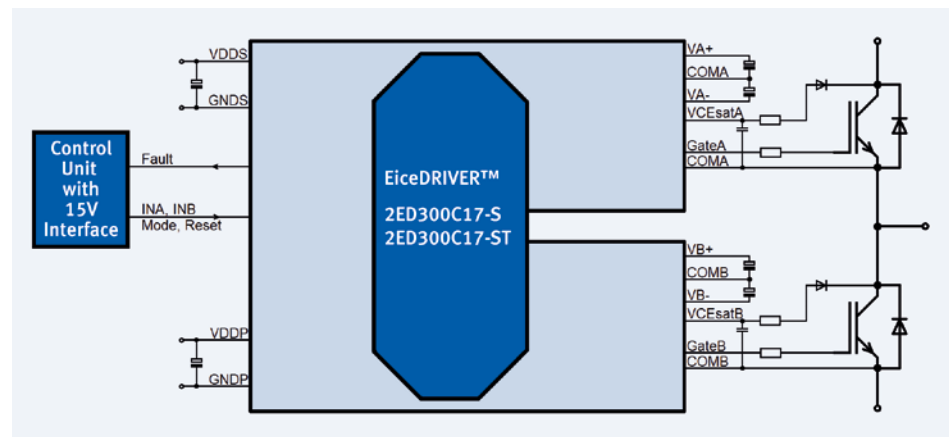


EiceDRIVER™ boards

Our EiceDRIVER™ board 2ED300C17-S/-ST is a dual-channel, high-voltage gate driver for all Infineon IGBT modules up to 1700V. These boards are ideally equipped to meet the high safety and reliability demands of wind energy systems.

This driver offers outstanding protection features and integrated fault management functionality to ensure safe operation. Desaturation monitoring is used to detect short circuits. A soft shut-down function prevents high switching overvoltages. Undervoltage lock-out (UVLO) avoids operation with gate voltages that are too low. Another important safety function is the reinforced isolation between the primary and secondary side.

Featuring two galvanically isolated channels, these devices can support two operating modes: direct mode and half-bridge mode. In half-bridge mode, an interlocking logic prevents cross-currents. In addition, the integrated isolated power supply allows simple paralleling of modules.



Key benefits

- Reinforced isolation according to EN 50178/ IEC 61800-5-1
- Reliable operation, also in harsh environments
- Patented paralleling of modules



EiceDRIVER™ Safe

Type	Channels	Control interface	IGBT max V_{CE} V	V_{ISO} kV	I_{GM} A	P_{OUT} W	T_{OP} °C	Size mm x mm	Mounting method	For modules
2ED300C17-S	2	15V CMOS logic	1700	5	±30	8	-25/85	60.5 x 72	Soldering	EconoPACK™+, 62 mm, IHM, EconoDUAL™, PrimePACK™
2ED300C17-ST	2	15V CMOS logic	1700	5	±30	8	-40/85	60.5 x 72	Soldering	EconoPACK™+, 62 mm, IHM, EconoDUAL™, PrimePACK™





EiceDRIVER™ ICs for pitch control units

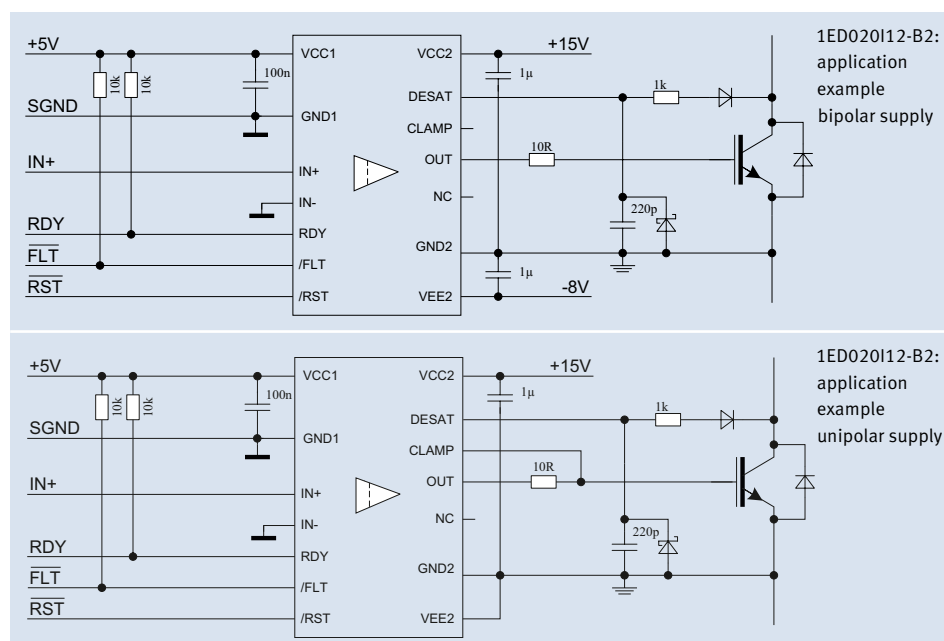
Our new enhanced EiceDRIVER™ family contains highly reliable, high-voltage driver ICs. By using advanced signal isolation technology, EiceDRIVER™ IGBT driver ICs overcome the temperature and lifetime restrictions associated with typical integrated IGBT driver solutions such as level-shifters and optocouplers. This makes them an ideal choice for demanding applications in wind turbine auxiliary drives like pitch control units.

The EiceDRIVER™ single-channel products 1ED020I12-F2 and 1ED020I12-B2 provide features such as desaturation detection (DESAT), active Miller Clamp, undervoltage lockout (UVLO) and shut-down in functional or basic isolation. Both devices 1ED020I12-FT and 1ED020I12-BT also support two-level turn-off (TLTO) for safe overcurrent shut-down. In 2ED020I12-F2, two independent channels are implemented in a compact package providing the same functions as 1ED020I12-F2.

Our EiceDRIVER™ high-voltage driver IC family covers a wide power range and enables customers to build reliable and efficient drive applications.

Key benefits

- Coreless transformer isolated driver
- Basic insulation according to DIN EN 60747-5-2
- Integrated protection features
- Suitable for operation at high ambient temperatures

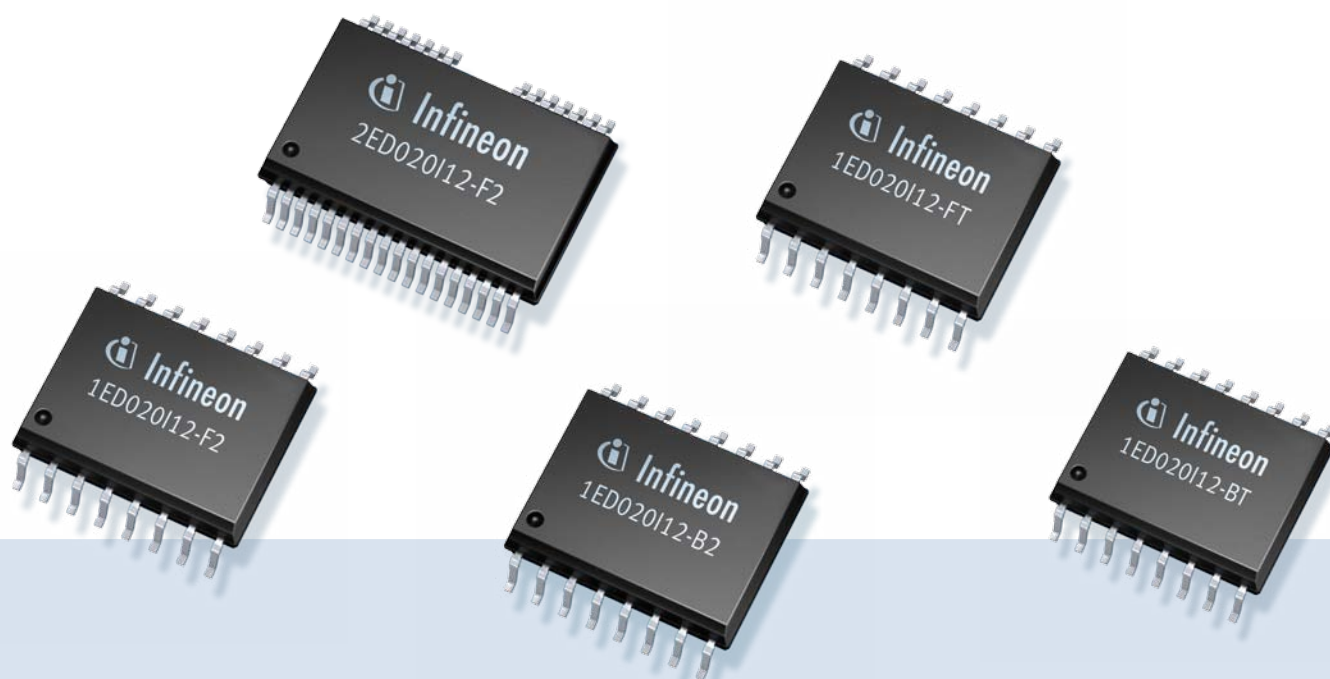




EiceDRIVER™ Enhanced

Product List	Technology	Max. voltage [V]	Input logic	Features	Basic * isolation	Typ. UVLO [V]	Package
1ED020I12-F2	1channel CLT	1200	Pos & neg	RST, DESAT, RDY	–	11 / 12	DSO-16
1ED020I12-B2	1channel CLT	1200	Pos & neg	RST, DESAT, RDY	X	11 / 12	DSO-16
1ED020I12-FT	1channel CLT	1200	Pos & neg	RST, DESAT, RDY, TLTO	–	11 / 12	DSO-16
1ED020I12-BT	1channel CLT	1200	Pos & neg	RST, DESAT, RDY, TLTO	X	11 / 12	DSO-16
2ED020I12-F2	2channel CLT	1200	Pos & neg	RST, DESAT, RDY	–	11 / 12	DSO-36

* Certified according to EN 60747-5-2

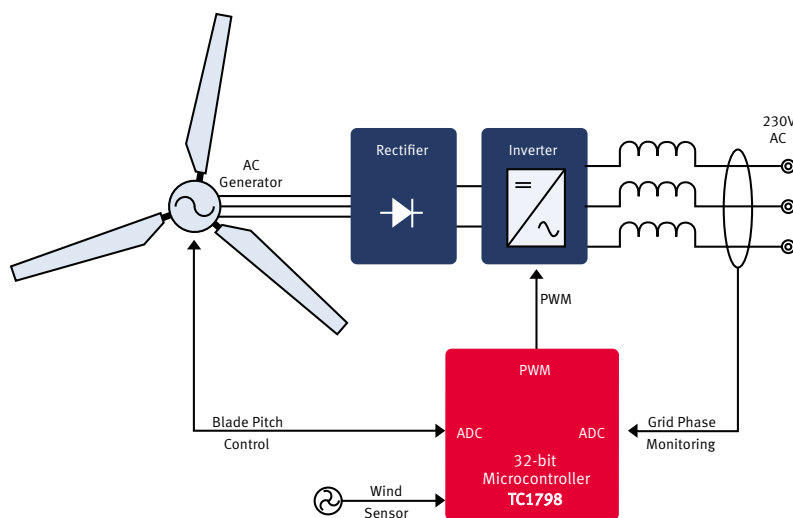




Microcontrollers

We offer a broad range of microcontrollers scaling from 8-bit models to multiple 32-bit cores targeted at embedded real-time applications. Our microcontrollers combine our fast embedded flash with an industry-leading peripheral set optimized for motor control and power conversion. By offering extended temperature ranges and outstanding reliability and quality, we can support all applications from touch control through blade pitch control to power conversion.

Our XMC4000 and latest TriCore™ families feature an integrated delta sigma demodulator for isolated current and voltage measurements. In combination with best-in-class PWM timers, this feature lineup supports all current and future power conversion topologies.



Key benefits

- Performance from ~10 to >1500 MIPS
- Embedded flash up to 4 MByte
- Temperature range up to +150°C
- High performance ADCs
- Integrated delta sigma demodulator
- Best-in-class PWM timer
- High-resolution PWM units

Our XMC4000 series benefits from the real-time control and signal-processing capabilities of the ARM® Cortex™-M4 CPU. It provides a set of modern communication interfaces such as Ethernet and USB plus HMI peripherals.

Auxiliary functions such as touch control or LED signage can be implemented using our cost-efficient microcontroller series XMC1000. The XMC1000 microcontrollers are based on the ARM® Cortex™-M0 and offer 32-bit performance at 8-bit pricing.



Power conversion & inverter control

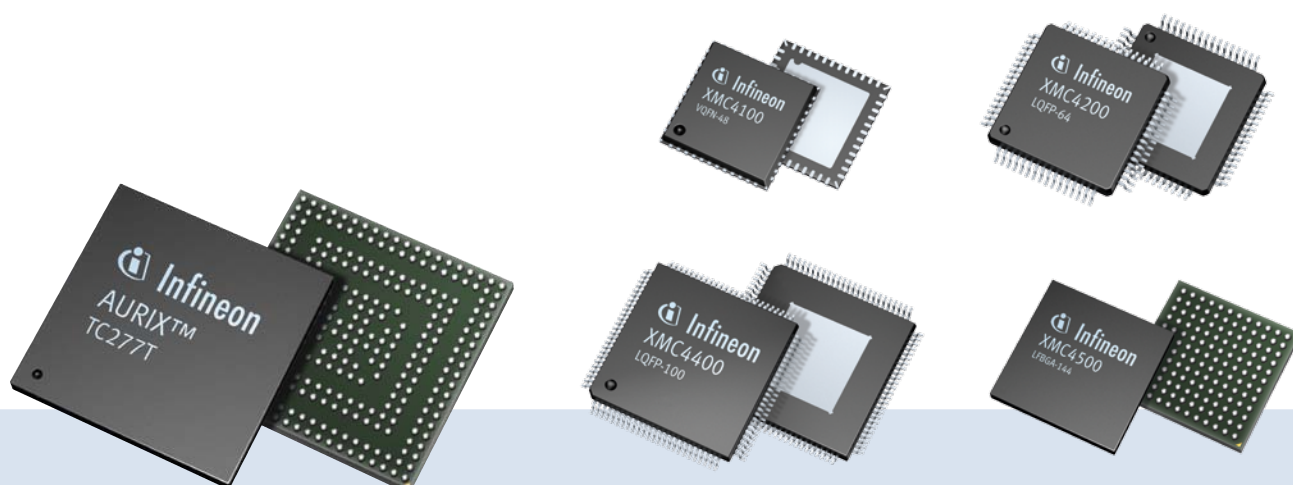
Part numbers	Core	Clock frequency	Memory flash/SRAM	Description
TC277, TC275	TriCore™	3x 200 MHz	4.4 MByte/472 KByte	AURIX™ series of multi-core MCUs, integrated DSP & lockstep functionality, highly accurate ADC & delta sigma ADC, programmable PWM timer, functional safety package
TC1793, TC1798	TriCore™	300 MHz	4.2 MByte/288 KByte	Single-core MCUs, integrated DSP functionality, highly accurate & fast ADCs, >100 PWM outputs
XMC4000	ARM® Cortex™-M4	120 MHz	1 MByte/160 KByte	Integrated DSP, highly accurate ADC & delta sigma ADC, programmable PWM timer, high-resolution PWM unit, motor control library available

Blade pitch control

Part numbers	Core	Clock frequency	Memory flash/SRAM	Description
XMC4000	ARM® Cortex™-M4	120 MHz	1 MByte/160 KByte	Integrated DSP, highly accurate ADC & delta sigma ADC, programmable PWM timer, motor control library available
XMC1300	ARM® Cortex™-M0	32/64 MHz	200 KByte/16 KByte	Cost-effective MCU for FOC motor control, 64 MHz MATH co-processor for advanced control loops (CORDIC / DIVIDE), programmable PWM, timer & fast ADC
XC800	8051	24 MHz	64 KByte/3 KByte	Cost-effective MCU for FOC motor control, integrated MATH co-processor, up to 150°C temperature range

HMI & communication

Part numbers	Core	Clock frequency	Memory flash/SRAM	Description
XMC4000	ARM® Cortex™-M4	120 MHz	1 MByte/160 KByte	Touch & LED control, display control library available, Ethernet, USB, SPI, etc.
XMC1200	ARM® Cortex™-M0	32 MHz	200 KByte/16 KByte	Cost-effective MCU with integrated touch & LED control, LED control unit for brightness & color control
XC800	8051	24 MHz	64 KByte/3 KByte	Low-cost MCU with integrated touch & LED control





High-precision integrated sensors

We develop sensors for a wide range of industrial applications, including renewable energy, industrial automation and e-mobility. Our offering here includes products such as magnetic position and speed sensors as well as linear Hall sensors. We offer a full range of energy-saving sensors for the fast-growing wind power sector.

Highly accurate & robust speed sensors

Our differential Hall sensor families TLE4957C(B) and TLE4951/54C(B) are the ideal choice for designers who need a robust speed sensor with high accuracy, air gap performance and vibration robustness. All devices in these families provide precise switching algorithms, dynamic self-calibration and excellent jitter and sensitivity levels, thus ensuring accurate speed measurements for both fine and coarse target wheels in the harshest of environments.

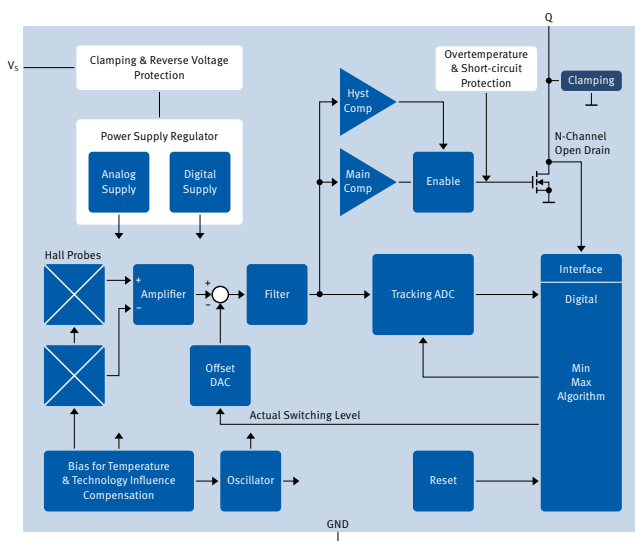
All of our sensors are designed to measure speed over a broad frequency range and come with sophisticated protective functionality. The TLE4957 family is a three-wire sensor with a voltage interface and is available with adaptive hidden or adaptive visible hysteresis. The TLE4951/54 family is a two-wire sensor with a current interface. In addition, TLE4954 provides direction information in four different protocol options. All sensors in the TLE4957, TLE4951 and TLE4954 families are available in our innovative iBB package and are ideal for industrial and automotive speed sensing applications.



Key benefits

Greater robustness against vibrations

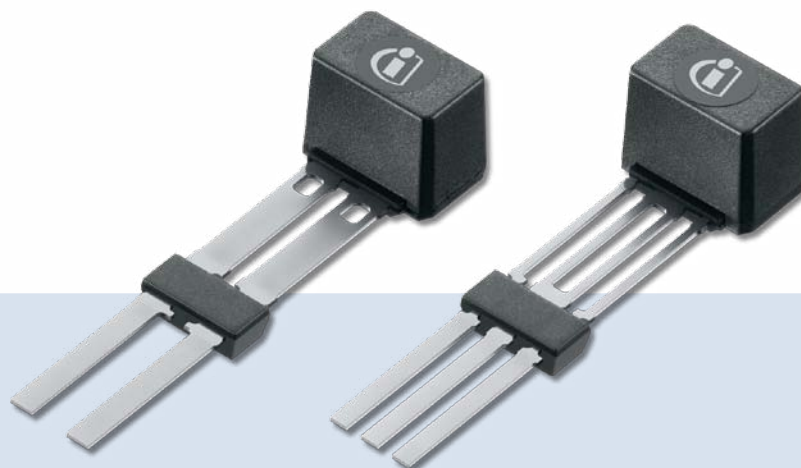
- Highly accurate speed measurements from 1 Hz to 12 kHz over large operating air gaps
- Broad operating temperature range
- High EMC robustness
- Reverse polarity protection
- AEC-Q100 qualified

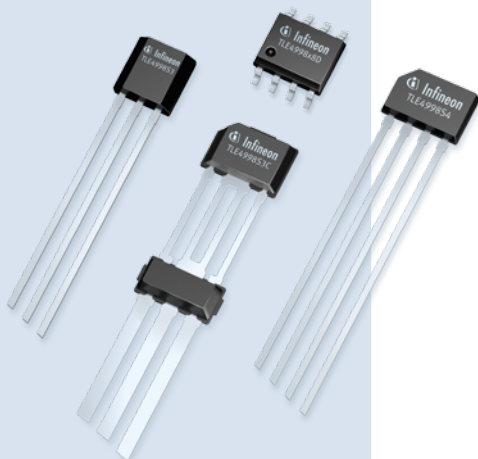




	Icon/ Description	TLE4921	TLE4924	TLE4926	TLE4927	TLE4928	TLE- 4941plusC	TLE4942	TLE4951 ³⁾	TLE4953	TLE4954 ³⁾	TLE4957	TLE5025	TLE5027
Automotive	Wheel speed						Yes	Yes						
	Camshaft		Yes		Yes								Yes	
	Crankshaft	Yes	Yes	Yes	Yes	Yes						Yes	Yes	Yes
	Transmission	Yes	Yes		Yes	Yes		Yes	Yes	Yes	Yes	Yes	Yes	Yes
Industrial		Yes	Yes		Yes				Yes		Yes	Yes		
Sensor technology		Diff. Hall	Diff. Hall	Diff. Hall	Diff. Hall	Diff. Hall	Diff. Hall	Diff. Hall	Diff. Hall	Diff. Hall	Diff. Hall	Diff. Hall	iGMR	iGMR
Improved air gap/jitter performance													Yes	Yes
Direction information available								Yes	Yes	Yes	Yes			Yes
vibration suppression algorithm Incl.									Yes	Yes	Yes	Yes		
Type of hysteresis ¹⁾		V	V	H	H	H	H	H	V	V	V	V/H	H	H
		F	A/F	F	A	F	F	F	A	A	A	A	A	A
Interface ²⁾	# of pins	4	3	3	3	3	2	2	2	2	2	3	3	3
	Interface	V	V	V	V	V	C	C	C	C	C	V	V	V
	Protocol	S	S	S	S	S	S	P	P	P	P	S	S	P
Package without integrated capacitor		Yes				Yes				Yes				
Package with integrated capacitor			Yes	Yes	Yes	Yes	Yes	Yes	Yes	Yes	Yes	Yes	Yes	Yes
iBB-Package			Yes		Yes		Yes		Yes		Yes	Yes		

¹⁾ H = Hidden; V = Visible; F = Fixed; A = Adaptive; P = Programmable | ²⁾ C = Current; V = Voltage interface; S = Single pulse; P = PWM protocol; A = AK protocol | ³⁾ Coming soon



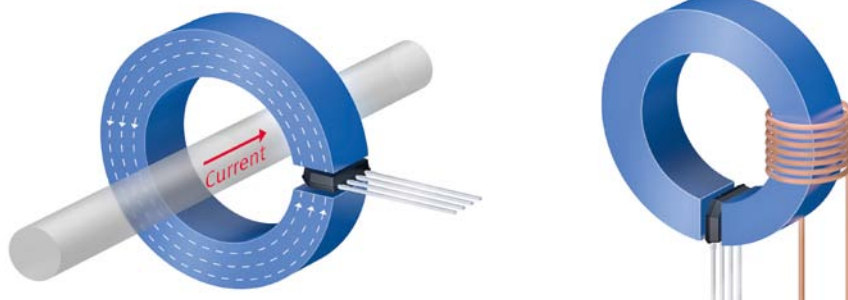


Linear Hall sensors

High-precision linear Hall sensors for current sensing

Our TLE4997/98 family of linear Hall ICs is tailored to the needs of highly accurate angular and linear position detection and current measurement applications. Each product measures the vertical component of a magnetic field and outputs a signal that is directly proportional to the magnetic field. Thanks to digital signal processing based on a 20-bit DSP architecture plus digital temperature compensation, these sensors deliver outstanding temperature stability compared with similar compensation methods. The TLE4998x products also come with a stress compensation feature to extend stability over lifetime and significantly reduce performance degradation.

The TLE4997/98 family offers a broad range of packages (including leaded and SMD options) and interface variants, giving engineers a large degree of design flexibility.



Flux concentrator (blue) surrounding the conductor. A Hall sensor is inserted in the air gap (left). The flux can be further boosted by using multiple windings on the principal conductor (right).

Key benefits

- Best-in-class accuracy with low drift of output signal over temperature and lifetime (including stress compensation in TLE4998)
- Programmable transfer function (gain, offset), clamping, bandwidth and temperature characteristics
- Broad range of interfaces (analog, PWM, SENT and SPC) and especially thin packages (SMD and leaded) available
- High reliability of sensors due to proven automotive zero-defect program

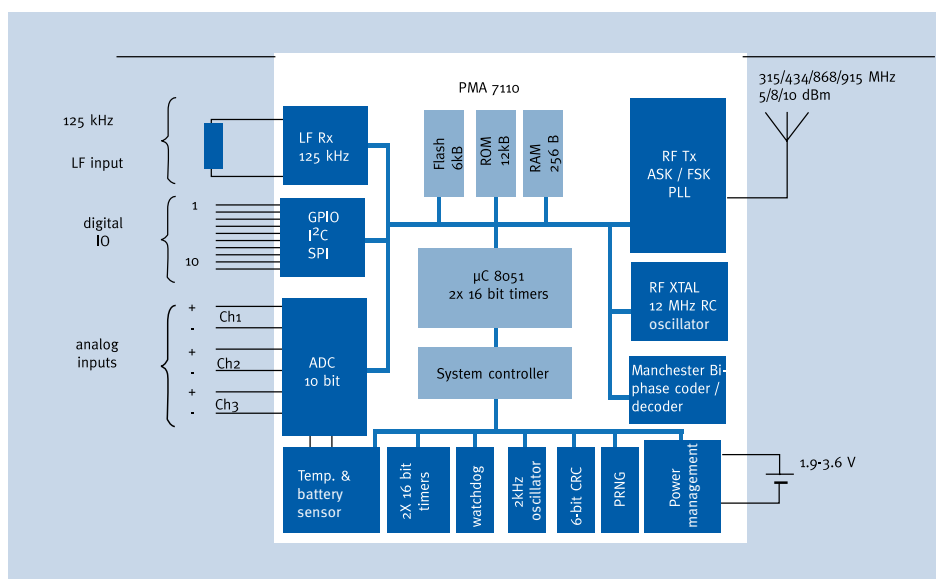
Product program	Memory	Number of pins	Magnetic sensitivity	Offset	Supply voltage (extended range)	ATV	Industrial	Package
TLE4997	EEPROM	3	± 12.5 to ± 300 mV/mT	$< \pm 400$ μ T	5V $\pm 10\%$ (7V)	•	•	PG-SSO-3-10 PG-TDSO-8
TLE4998P	EEPROM	3	± 0.2 to $\pm 6\%$ /mT	$< \pm 400$ μ T	5V $\pm 10\%$ (16V)	•	•	PG-SSO-3-10 PG-SSO-4-1 PG-SSO-3-9 (2 capacitors) PG-TDSO-8
TLE4998S	EEPROM	3	± 8.2 to ± 245 LSB/mT	$< \pm 400$ μ T	5V $\pm 10\%$ (16V)	•	•	PG-SSO-3-10 PG-SSO-4-1 PG-SSO-3-9 (2 capacitors) PG-TDSO-8
TLE4998C	EEPROM	3	± 8.2 to ± 245 LSB/mT	$< \pm 400$ μ T	5V $\pm 10\%$ (16V)	•	•	PG-SSO-3-10 PG-SSO-4-1 PG-SSO-3-9 (2 capacitors) PG-TDSO-8



SmartLEWISTM MCU

SmartLEWISTM – transmitters with embedded microcontrollers

Our SmartLEWISTM family of PMA51xx/PMA71xx microcontrollers comprises an ASK/FSK transmitter for sub-1GHz ISM frequency bands plus an embedded 8051 microcontroller, on-chip flash memory and other exciting peripherals. These highly optimized, single-chip ICs are ideal, for example, for remote control designs, requiring only eleven components to create a key FOB. An associated software library provides powerful functions such as AES encryption, thus enabling fast software development and reduced user code size. The PMA family also offers an optional integrated 125 kHz LF receiver, which can be used for wireless wake-up, or an integrated 10-bit ADC to directly connect an analog sensor.

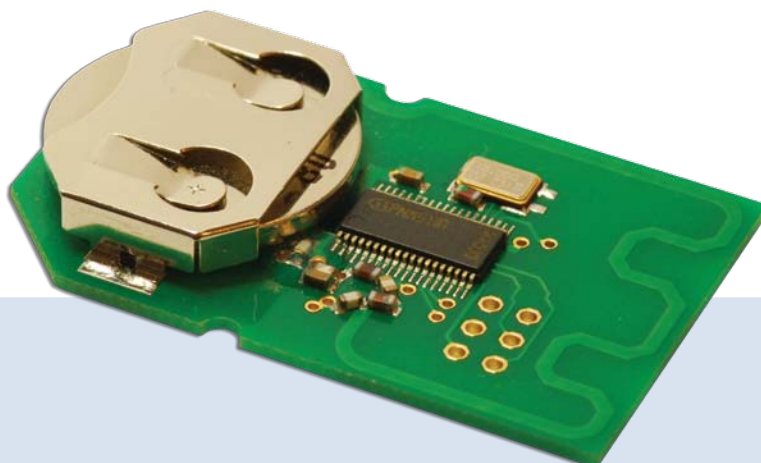


Key Benefits

- Highest functionality and performance
- Multiband transmitter plus embedded 8051 microcontroller with 6 KByte flash for user code and 2 x 128 Byte RAM for EEPROM emulation
- Comprehensive software library in ROM including license-free encryption algorithms such as AES-128
- Programmable transmitter power levels of 5, 8 and 10 dBm
- 125 kHz LF ASK receiver for wireless wake-ups
- 3-channel, 10-bit ADC
- Integrated temperature and supply voltage sensors

Easy design

- Quick-start development kit with USB interface
- Key FOB reference design with example software (PMA FOB)





IPOSIM

The Infineon POver SIMulation (IPOSIM) program is designed to help customers select the right Infineon bipolar products for their rectifier (B2, B6, M3.2 and M6) or AC switch (W1C and W3C) applications. It also helps engineers select suitable IGBT modules for inverter (single- & three-phase in 2-level as well as 3-level) or DC converter (buck and boost) applications.

IPOSIM calculates switching and conduction losses for active components in power semiconductor modules by taking into account static and dynamic module parameters as well as thermal ratings. Cooling conditions are custom-specified, but default values are also available. Junction temperatures as a result of applied loads for specific inverter operation points are calculated. IPOSIM also runs calculations for complete load cycles. Results are shown in tables and plotted as charts. Both can be saved for later review or printed as PDF files. For optimum accuracy and convenience, different control algorithms can be applied.

IPOSIM is quick and easy to use, enabling each engineer to select the best Infineon product for their application, also working out the applicable semiconductor power losses to establish the expected service life.

Visit the website and run a sample calculation yourself.

web.transim.com/Infineon-IPOSIM

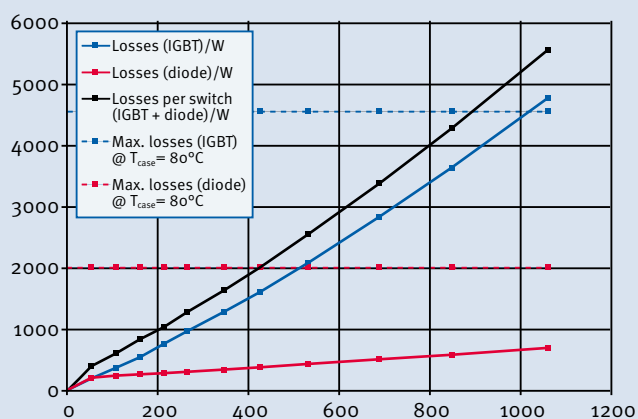


IPOSIM calculation results

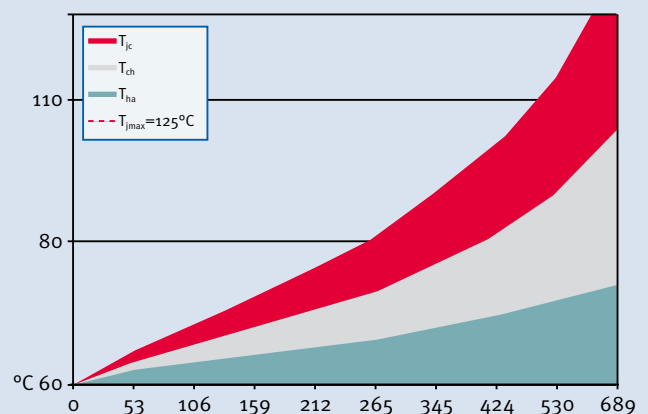
Selected module IHV 6.5 kV 140 x 190	FZ750R65KE3
Input	
DC link voltage V _{dc}	3600 V
Frequency f ₀	50 Hz
Switching frequency f _s	400 Hz
Modulation factor m	1
Cos φ	1
Operation point current I _{rms}	600 A
Thermal input	
Max. junction temperature T _j	125°C
Max. ambient temperature T _a	60°C
R _{th} heat sink per arm	0,006 K/W

Losses at 600 A	IGBT	Diodes
Static losses	859 W	74 W
Dynamic losses	1541 W	405 W
Total losses	2400 W	478 W
Temperatures at 600 A	IGBT	ripple Δ T _j [K]
T _{jmax}	122.3°C	
T _{jmin}	116.7°C	5,5 K
T _c	98.6°C	
T _{hs}	77.4°C	

IGBT power simulation



Average losses for sinusoidal output current at 400 Hz switching frequency



Temperature distribution across IGBT junction-to-case, case-to-heat sink and heat sink-to-ambient for T_a = 60°C and a given heat sink

Ask Infineon. Get connected with the answers.

Where you need it. When you need it.

Infineon offers its toll-free 0800/4001 service hotline as one central number, available 24/7 in English, Mandarin and German.

Our global connection service goes way beyond standard switchboard services by offering qualified support on the phone. Call us!

- Germany 0800 951 951 951 (German/English)
- China, mainland 4001 200 951 (Mandarin/English)
- India 000 800 4402 951 (English)
- USA 1-866 951 9519 (English/German)
- Other countries 00* 800 951 951 951 (English/German)
- Direct access +49 89 234-0 (interconnection fee, German/English)

* Please note: Some countries may require you to dial a code other than "00" to access this international number, please visit www.infineon.com/service for your country!

Where to Buy

Infineon Distribution Partners and Sales Offices

Please use our location finder to get in contact with your nearest Infineon distributor or sales office.

www.infineon.com/WhereToBuy

Infineon Technologies – innovative semiconductor solutions for energy efficiency, mobility and security.



Published by
Infineon Technologies AG
85579 Neubiberg, Germany

© 2013 Infineon Technologies AG.
All Rights Reserved.

Visit us:
www.infineon.com

Order Number: B133-H9795-X-X-7600
Date: 04 / 2013

ATTENTION PLEASE!

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics ("Beschaffheitsgarantie"). With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation warranties of non-infringement of intellectual property rights of any third party.

INFORMATION

For further information on technology, delivery terms and conditions and prices please contact your nearest Infineon Technologies Office (www.infineon.com).

WARNINGS

Due to technical requirements components may contain dangerous substances. For information on the types in question please contact your nearest Infineon Technologies Office. Infineon Technologies Components may only be used in life-support devices or systems with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system, or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body, or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.